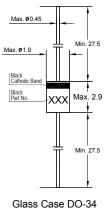
SILICON EPITAXIAL PLANAR DIODE

High voltage switching



Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	V _R	220	V
Mean Rectifying Current	Io	200	mA
Peak Forward Current	I _{FM}	625	mA
Surge Current (1 s)	I _{surge}	1	Α
Power Dissipation	P _{tot}	300	mW
Junction Temperature	T _j	175	°C
Storage Temperature Range	T _S	- 65 to + 175	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 200 mA	V _F	1.5	V
Reverse Current at V _R = 220 V	I _R	10	μΑ
Capacitance between Terminals at f = 1 MHz	Ст	3	pF
Reverse Recovery Time at I_R = 20 mA, I_F = 20 mA, R_L = 50 Ω	t _{rr}	75	ns

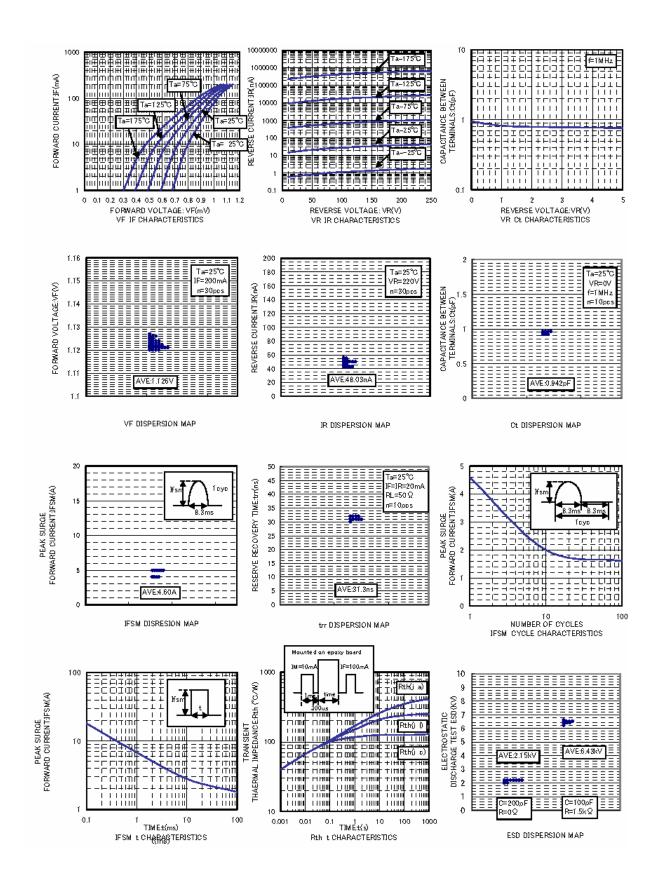








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